

IN THE SPECIFICATION:

Please amend the paragraph, beginning at line 5 of page 8 to read as follows.

Next, the separation layer 100 is partitioned to desired semiconductor elements and/or semiconductor integrated circuits by kerfs to form chips (Fig. 1D), thereby obtaining one or a plurality of thin-film semiconductor devices 350. ~~Then, cracks in the planar direction are formed in the separation layer 100 to separate the thin-film semiconductor devices 350 as chips from the member 120.~~ The bottom surface of each kerf in Fig. 1D need not always reach the adhesive layer 310. For example, the support member 300 is made of a stretchable material. In this case, even when the semiconductor film 110 is not completely separated, the chips can be extracted by stretching the support member 300.